

**Silicon PNP Power Transistors****2SA1859 2SA1859A****DESCRIPTION**

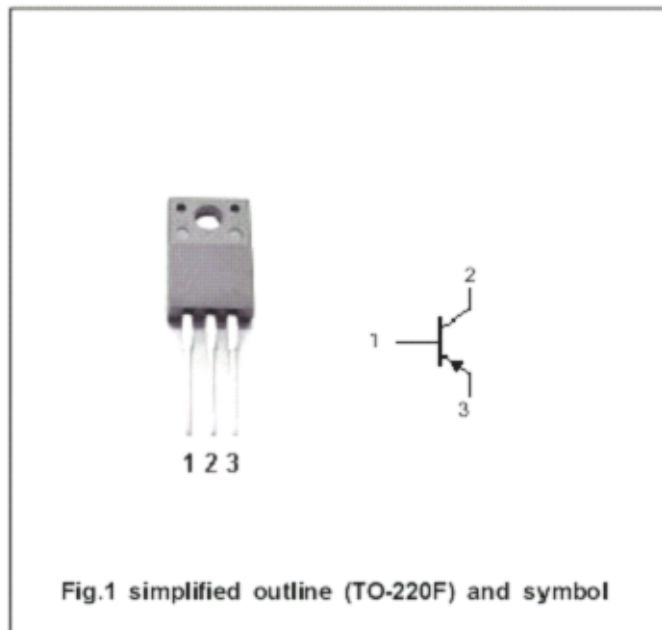
- With TO-220F package
- Complement to type 2SC4883/4883A

APPLICATIONS

- For audio output driver and TV velocity-modulation applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Absolute maximum ratings (Ta=25℃)**

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	2SA1859	Open emitter	-150	V
		2SA1859A		-180	
V _{CE0}	Collector-emitter voltage	2SA1859	Open base	-150	V
		2SA1859A		-180	
V _{EB0}	Emitter-base voltage		Open collector	-6	V
I _C	Collector current			-2	A
I _B	Base current			-1	A
P _C	Collector dissipation		T _C =25℃	20	W
T _j	Junction temperature			150	℃
T _{stg}	Storage temperature			-55~150	℃



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2SA1859 2SA1859A

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SA1859	I _C =-10mA; I _B =0	-150			V
		2SA1859A		-180			
V _{CEsat}	Collector-emitter saturation voltage		I _C =-0.7A; I _B =-70mA			-1.0	V
I _{CBO}	Collector cut-off current	2SA1859	V _{CB} =-150V; I _E =0			-10	μA
		2SA1859A	V _{CB} =-180V; I _E =0			-10	μA
I _{EB0}	Emitter cut-off current		V _{EB} =-6V; I _C =0			-10	μA
h _{FE}	DC current gain		I _C =-0.7A; V _{CE} =-10V	60		240	
f _T	Transition frequency		I _C =-0.7A; V _{CE} =-12V		60		MHz
C _{OB}	Output capacitance		I _E =0; V _{CB} =-10V; f=1MHz		30		pF

Switching time

t _{on}	Turn-on time	I _C =-1A; I _{B1} =-I _{B2} =-0.1A V _{CC} =-20V, R _L =20Ω		0.50		μs
t _s	Storage time			1.00		μs
t _f	Fall time			0.50		μs



PACKAGE OUTLINE

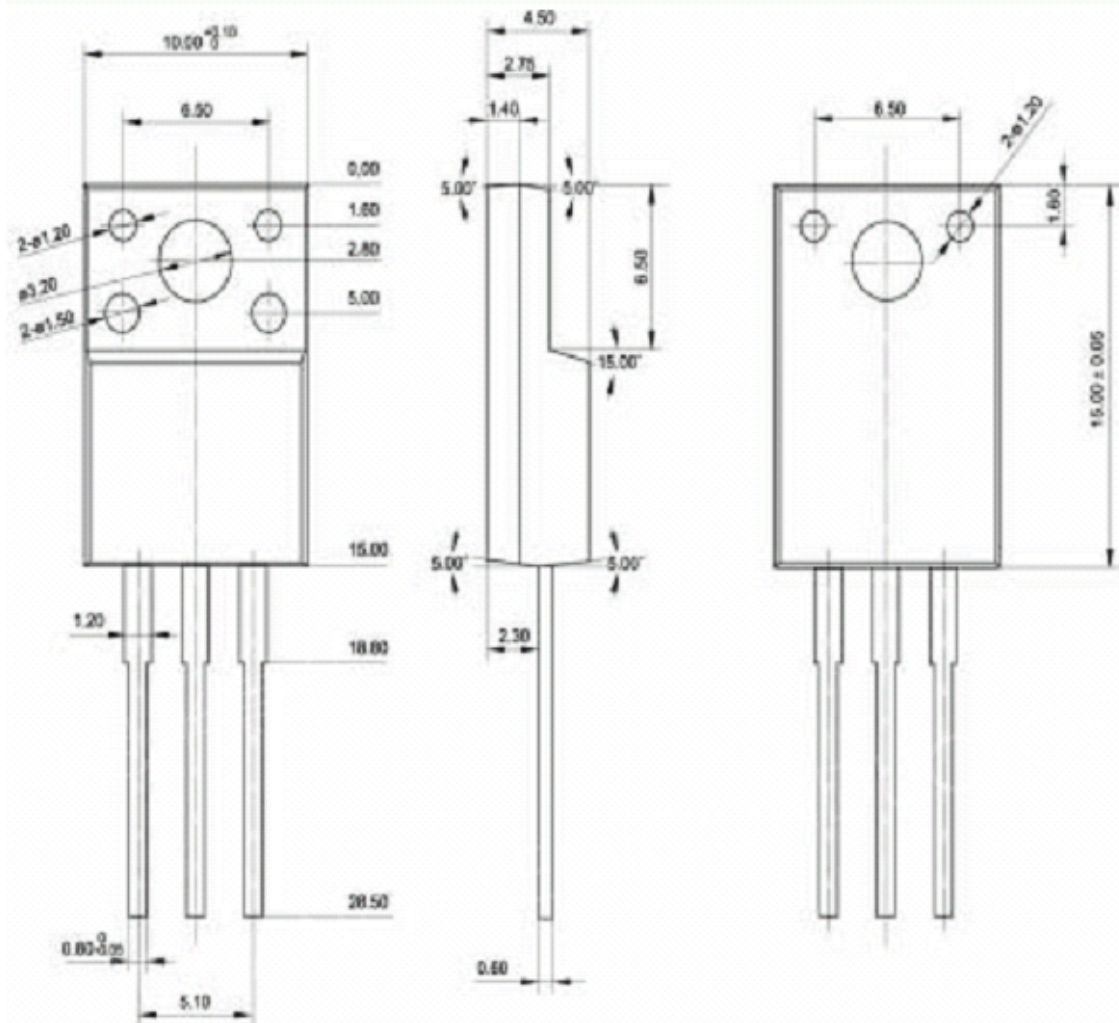


Fig.2 Outline dimensions



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2SA1859 2SA1859A

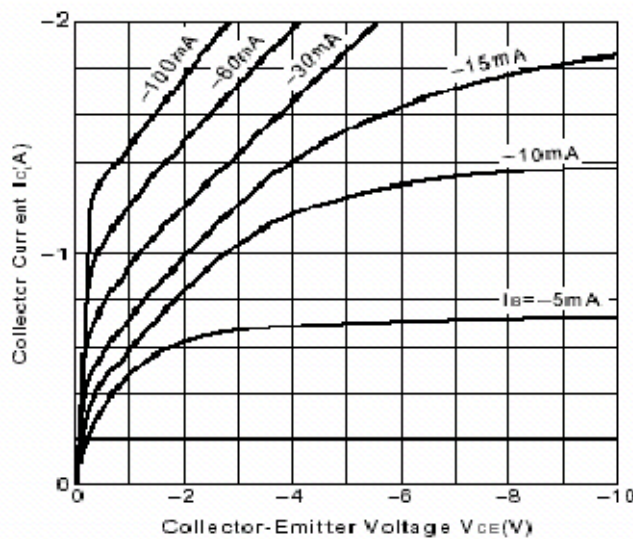


Fig.3 Static Characteristic

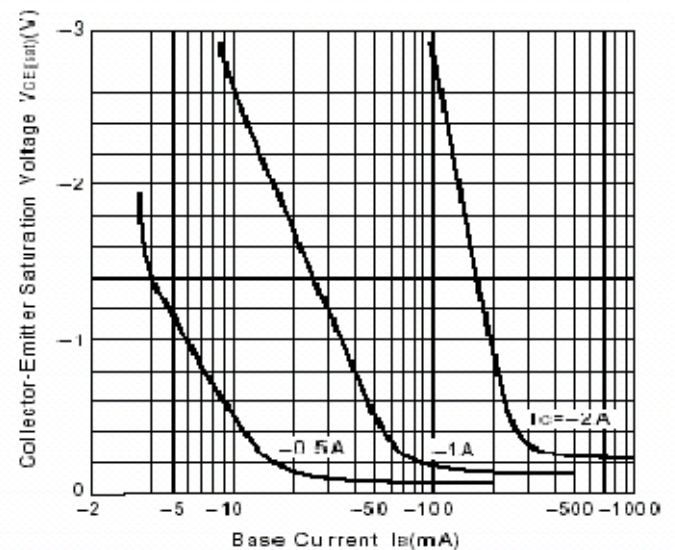


Fig.4 $V_{ce(sat)}$ - I_b Characteristics

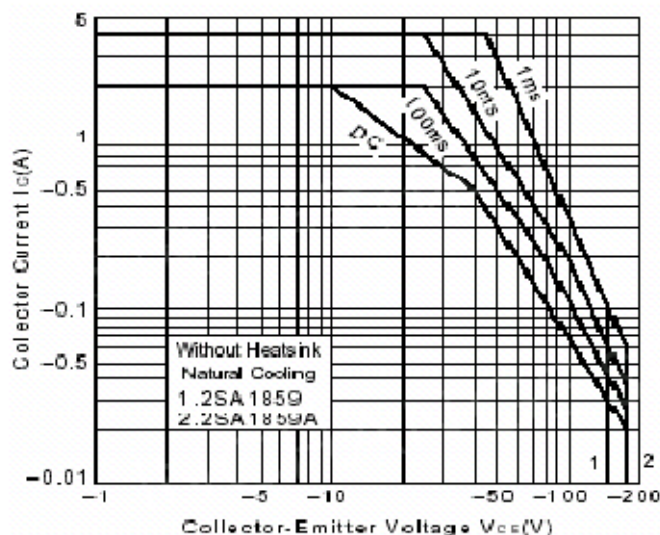


Fig.5 Safe Operating Area

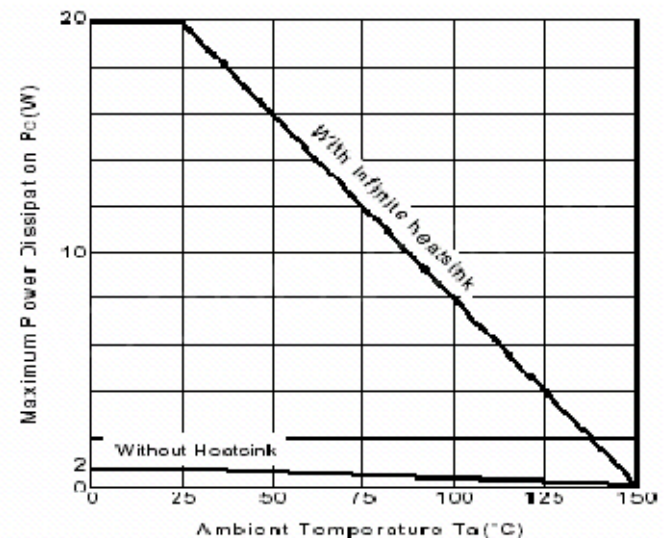


Fig.6 Power Derating

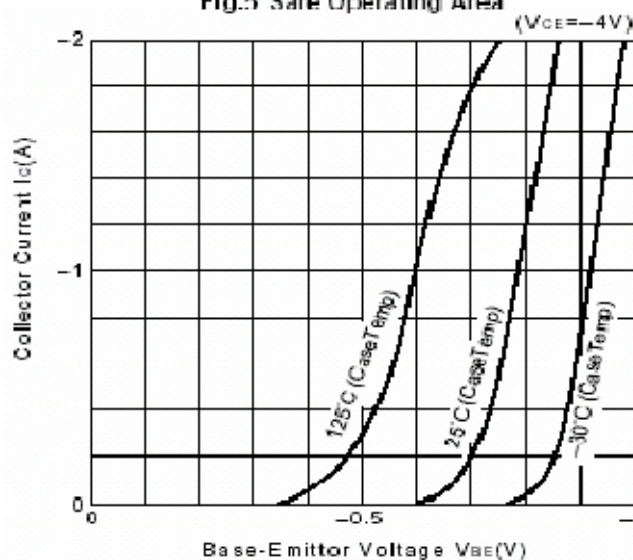


Fig.7 I_c - V_{be}

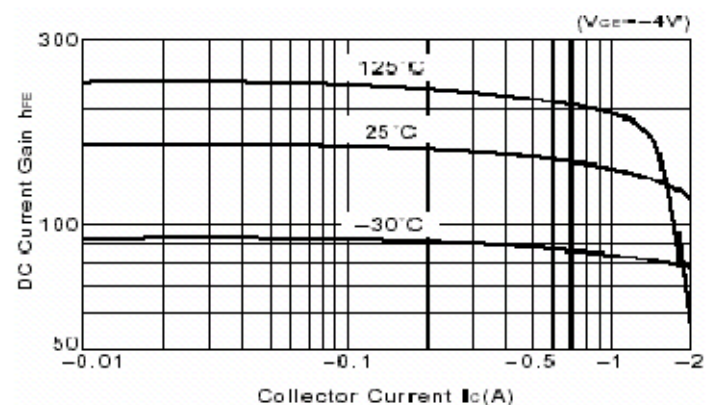


Fig.8 DC current Gain